

Appl. No. 10/662,850
Reply to Office action of 08/25/2004

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-19 (Canceled).

20. (Currently Amended) A method of fabricating a composite nitride cap comprising:
providing an NMOS semiconductor device having active regions, a channel region and a polysilicon gate;
forming a liner layer over at least a portion of the semiconductor device; and
forming an upper layer on the liner layer wherein the upper layer is substantially thicker than the liner layer and is comprised substantially of nitride, wherein said upper layer further comprises a hydrogen concentration greater than about atomic 15%.

21. (Currently Amended) The method of claim 20, further comprising A method of fabricating a composite nitride cap comprising:
providing an NMOS semiconductor device having active regions, a channel region and a polysilicon gate;
forming a liner layer over at least a portion of the semiconductor device;
forming an upper layer on the liner layer wherein the upper layer is substantially thicker than the liner layer and is comprised substantially of nitride; and
causing dopants to segregate out of an Si/SiO₂ interface in the channel region during an annealing process.

Claims 22-24 (Canceled).